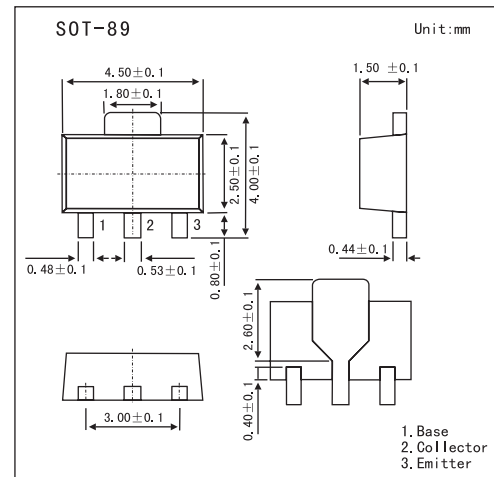


PNP Epitaxial Planar Silicon Transistors

2SB1119

■ Features

- Very small size making it easy to provide highdensity, small-sized hybrid IC:s.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-25	V
Collector-emitter voltage	V _{CEO}	-25	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-1	A
Collector current (pulse)	I _{CP}	-2	A
Collector dissipation	P _C	500	mW
Jumction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = -20V , I _E = 0			-0.1	μA
Emitter cutoff current	I _{EBO}	V _{CB} = -4V , I _E = 0			-0.1	μA
DC current Gain	h _{FE}	V _{CE} = -2V , I _C = -50mA	100		560	
		V _{CE} = -2V , I _C = -1A	40			
Gain bandwidth product	f _T	V _{CE} = -10V , I _C = -50mA		180		MHz
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -500mA , I _B = -50mA		-0.15	-0.7	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -500mA , I _B = -50mA		-0.85	-1.2	V
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -10μA , I _E = 0	-25			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA , R _{BE} = ∞	-25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -10μA , I _C = 0	-5			V
Output capacitance	C _{ob}	V _{CB} = -10V , f = 1MHz		52		pF

■ hFE Classification

Marking	BB			
Rank	R	S	T	U
hFE	100~200	140~280	200~400	280~560